Honeywell's Docket No. 30-4899 (4780) Practitioner's Docket No. 595.06-US1

ABSTRACT

A damascene structure includes a hard mask layer that is applied in a liquid phase to a line dielectric layer. Contemplated hard mask layers comprise a Si-N bond and are densified such that the etch resistivity of the hard mask layer is greater than the etch resistivity of the line dielectric layer and the via dielectric layer in the damascene structure. Particularly preferred hard mask layers include polyperhydrosilazane.